

700V 4A N-Channel Super Junction Power MOSFET

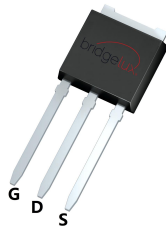
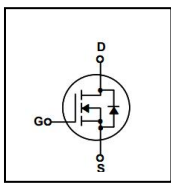
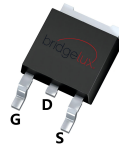
FEATURES

- $R_{DS(ON)} \leq 1 \Omega$ @ $V_{GS}=10V, I_D=2A$
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Fast switching capability
- Lead free product is acquired

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

SYMBOL


TO-251L

TO-252

TO-220F

ASSEMBLY MESSAGE

Product Name	Package	Packaging
BXC70R1K0U	TO-251L	Tube
BXC70R1K0D	TO-252	Tube/Reel
BXC70R1K0F	TO-220F	Tube

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Rating		Unit
			BXC70R1K0U/D	BXC70R1K0F	
Drain-Source Voltage		V_{DSS}	700		V
Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	I_D	4		A
	Continuous ($T_C = 100^\circ\text{C}$)		2.7		A
Drain Current	Pulsed (Note1)	I_{DM}	16		A
Gate-Source Voltage		V_{GSS}	± 30		V
Avalanche Energy	Single Pulse (Note2)	E_{AS}	50		mJ
Avalanche Current (Note1)		I_{AR}	0.9		A
Power Dissipation (Note 2)	$T_C = 25^\circ\text{C}$	P_D	44.64	28.41	W
	Derate above 25°C		0.36	0.23	W/ $^\circ\text{C}$
Maximum Junction Temperature		T_J	150		$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 to 150		$^\circ\text{C}$

Note: 1. Limited by maximum junction temperature, maximum duty cycle is 0.75
 2. $L=5\text{mH}$, $V_{DD}=50\text{V}$, $R_G=25 \Omega$, Starting $T_J = 25^\circ\text{C}$

THERMAL CHARACTERISTICS

Parameter	Symbol	Max.		Unit
		BXC70R1K0U/D	BXC70R1K0F	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.8	4.4	°C / W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62	73	°C / W

ELECTRICAL CHARACTERISTICS ($T_J=25^{\circ}\text{C}$, unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	VGS=0V, ID=250 μ A	700			V
Zero Gate Voltage Drain Current	I_{DSS}	VDS=700V, VGS=0V			1	μ A
		VDS=560V, TC = 125°C		10		μ A
Gate-Body Leakage Current, Forward	I_{GSS}	VGS=30V			100	nA
Gate-Body Leakage Current, Reverse		VGS=-30V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	VDS=VGS, ID=250 μ A	2.5		4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	VGS=10V, ID=2A		0.88	1	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	VDS=100V, VGS=0V, f=1.0MHz		309		pF
Output Capacitance	C_{OSS}			18		pF
Reverse Transfer Capacitance	C_{RSS}			1		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{D(ON)}$	VDD=400V, ID=2A, VGS = 10V ,RG=25 Ω		9.3		ns
Turn-ON Rise Time	t_R			23		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			36		ns
Turn-OFF Fall-Time	t_F			26		ns
Total Gate Charge(Note5)	Q_G	VDD =560V, VGS =10V, ID =2A		9.3		nC
Gate Source Charge	Q_{GS}			2		nC
Gate Drain Charge	Q_{GD}			4		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	IF=2A, VGS=0V		0.85		V
Diode Continuous Forward Current	I_S				4	A
Pulsed Drain-Source Current	I_{SM}				16	A
Reverse Recovery Time	t_{RR}	VR = 50 V, IF = 2A di/dt=100 A/ μ s		162		ns
Reverse Recovery Charge	Q_{RR}			0.92		μ C

TYPICAL CHARACTERISTICS

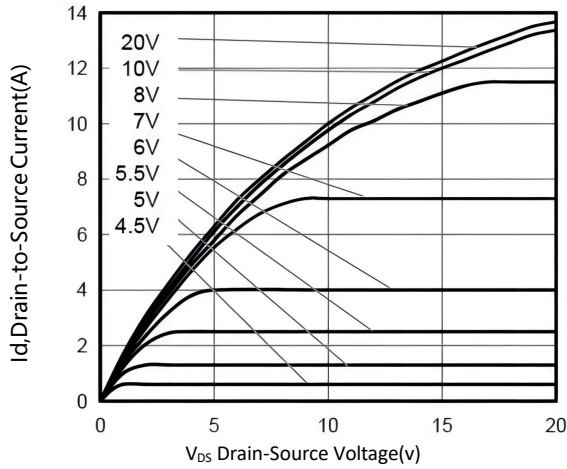


Figure1. Typical Output Characteristics

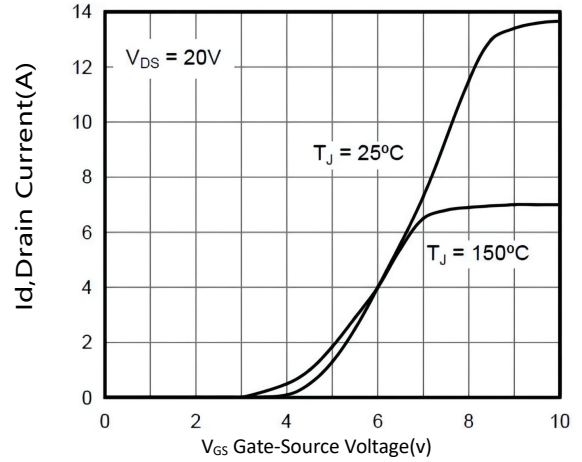


Figure2. Typical Transfer Characteristics

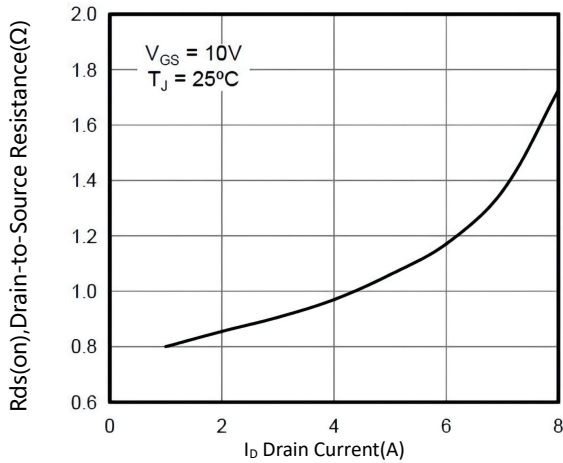


Figure3. On-Resistance versus Drain Current

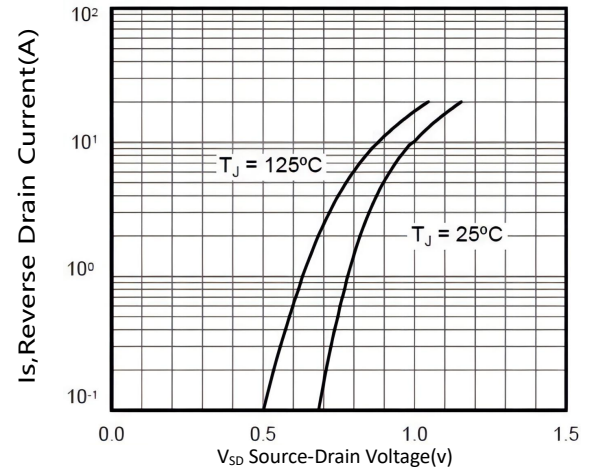


Figure4. Diode forward voltage versus Current

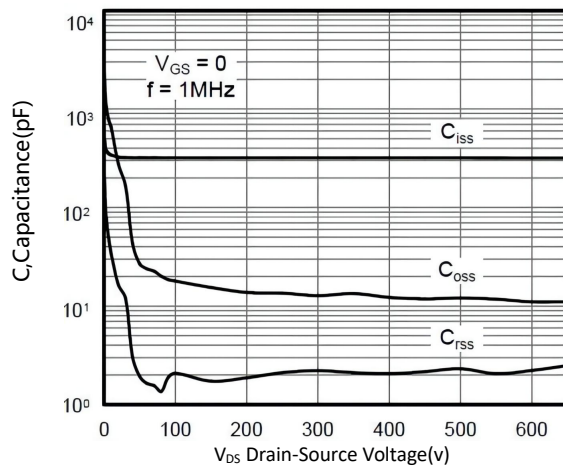


Figure5. Typical Capacitance versus VDS

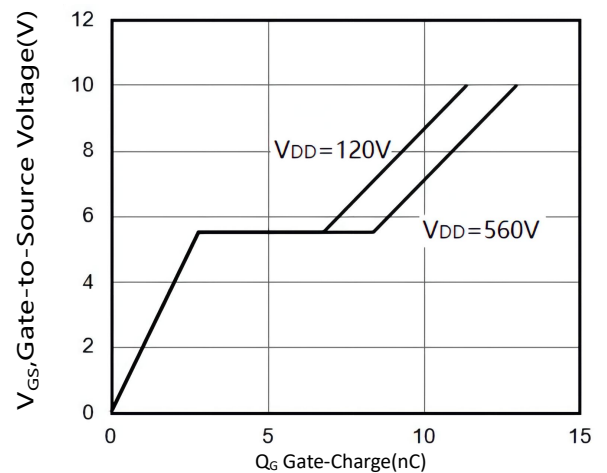


Figure6. Typical Gate Charge versus VGS

TYPICAL CHARACTERISTICS(Cont.)

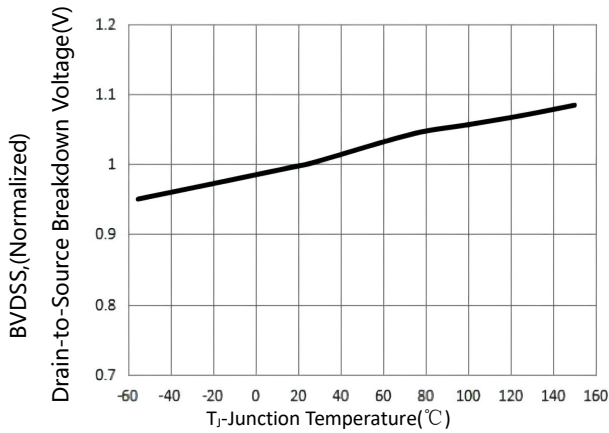


Figure7. BV_{DSS} Variation with Temperature

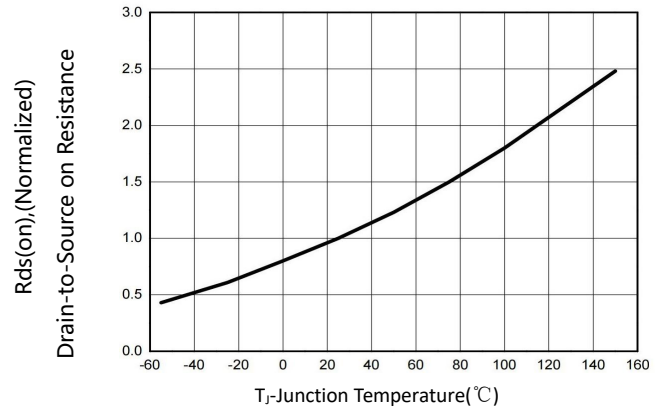
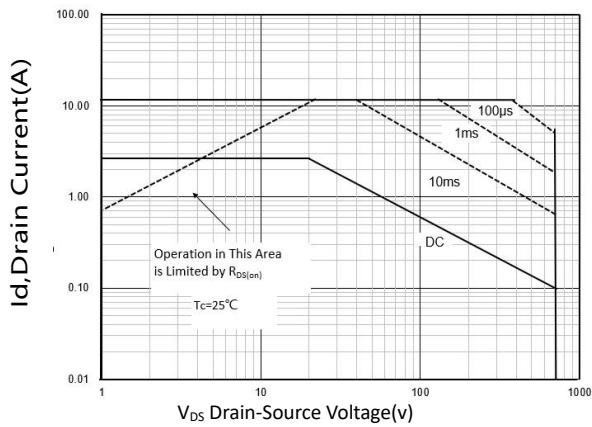
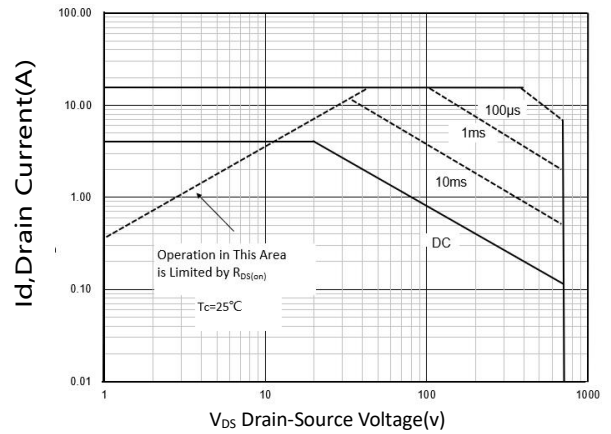


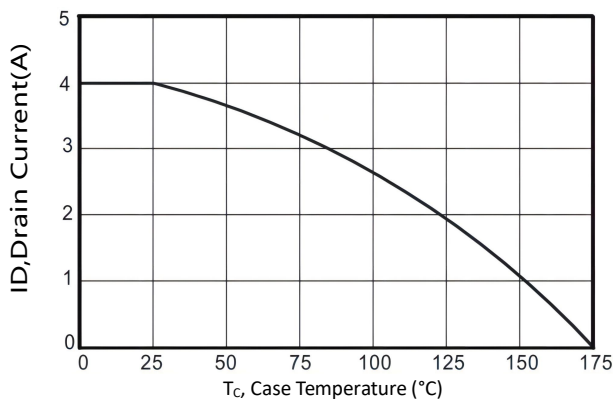
Figure8. On-Resistance Variation with Temperature



**Figure9. Maximum Safe Operating Area
BXC70R1K0U/D**

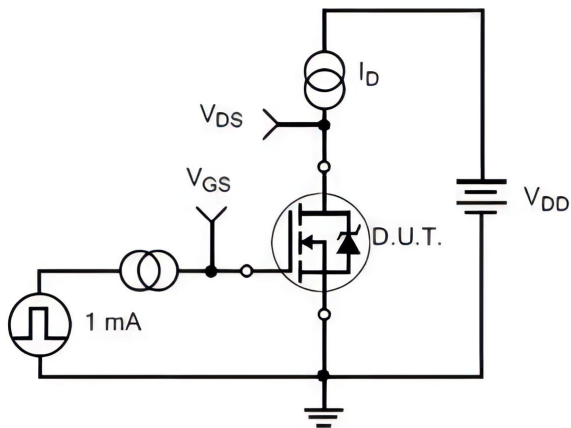


**Figure9. Maximum Safe Operating Area
BXC70R1K0F**

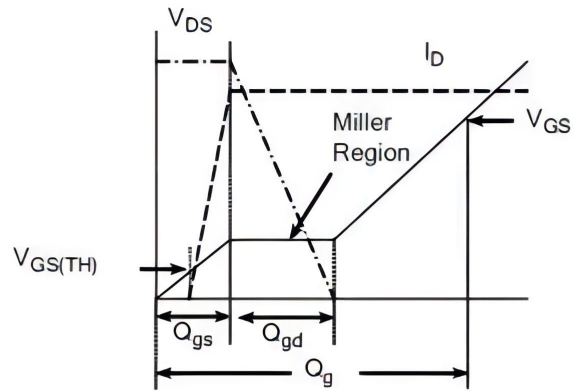


**Figure10. Maximum Continuous Drain Current
versus Case Temperature**

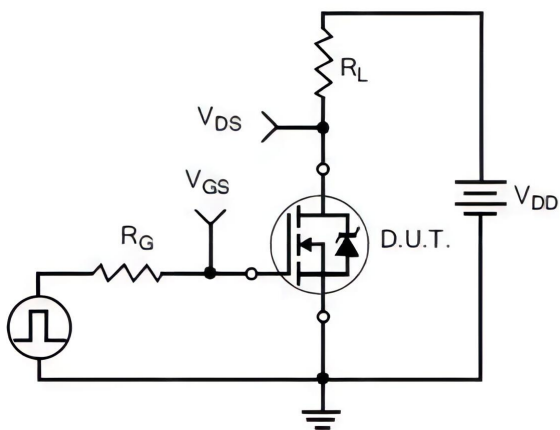
TEST CIRCUITS AND WAVEFORMS



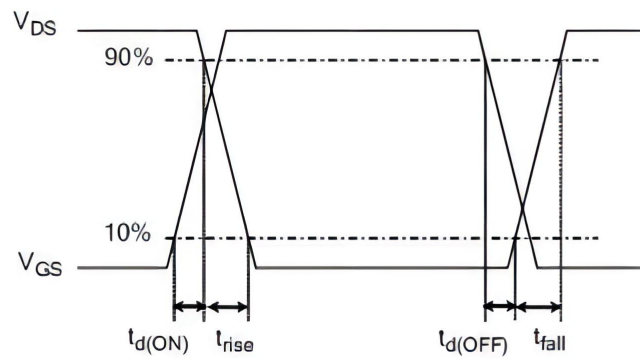
Gate Charge Test Circuit



Gate Charge Waveform

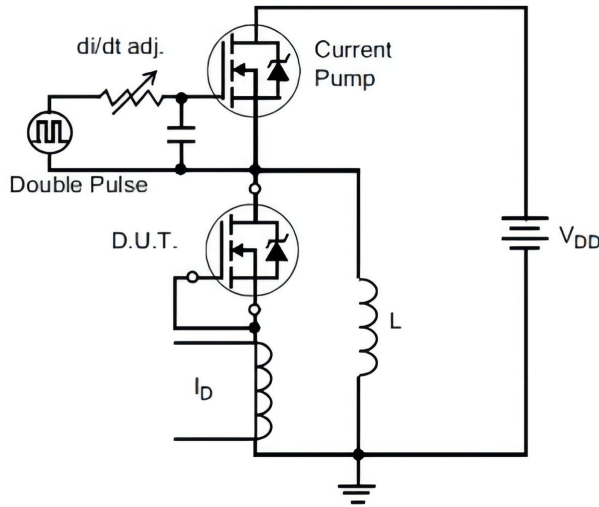


Resistive Switching Test Circuit

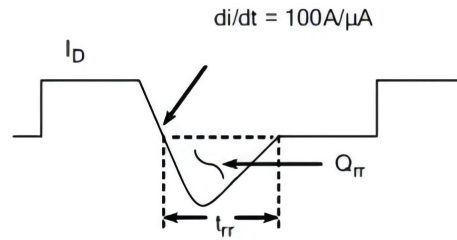


Resistive Switching Waveforms

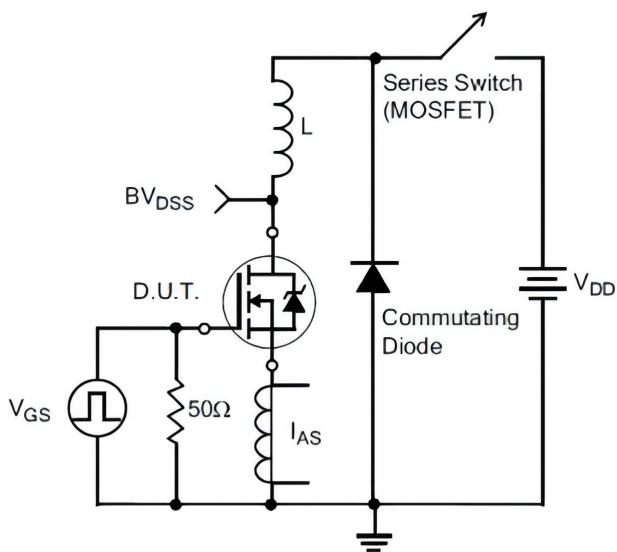
TEST CIRCUITS AND WAVEFORMS(Cont.)



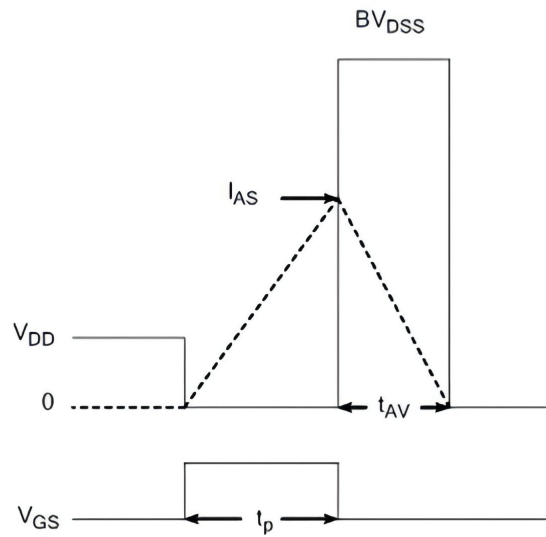
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit



$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

Unclamped Inductive Switching Waveforms

Revision history

Document revision history

Date	Revision	Changes
29-Sep-2021	1.0	First release

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